## **SPTECH Silicon PNP Power Transistor**

## TIP36C

#### **DESCRIPTION**

- DC Current Gain-
- :  $h_{FE} = 25(Min)@I_C = -1.5A$
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -100V(Min)
- Complement to Type TIP35C
- · Current Gain-Bandwidth Product-
  - :  $f_T = 3.0MHz(Min)@I_C = -1.0A$

#### **APPLICATIONS**

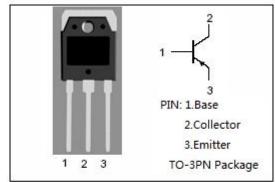
• Designed for use in general purpose power amplifier and switching applications.

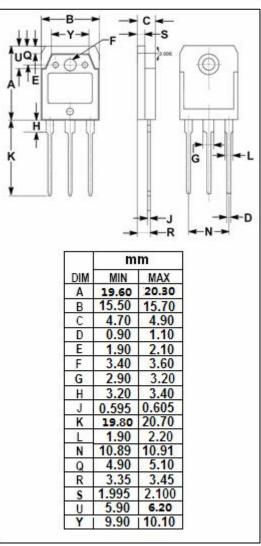
### ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current-Continuous	-25	Α
I <sub>CM</sub>	Collector Current-peak	-40	Α
Ι <sub>Β</sub>	Base Current	-5	А
Pc	Collector Power Dissipation@Tc=25°C	125	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	T <sub>stg</sub> Storage Temperature Range -65		$^{\circ}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.0	°C/W





1

# **SPTECH Silicon PNP Power Transistor**

TIP36C

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	Ic= -30mA ;I <sub>B</sub> = 0	-100		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -15A ;I <sub>B</sub> = -1.5A		-1.8	V
VCE(sat)-2	Collector-Emitter Saturation Voltage	Ic= -25A; I <sub>B</sub> = -5A		-4.0	V
VBE(on)-1	Base-Emitter On Voltage	Ic= -15A ; VcE= -4V		-2.0	V
V <sub>BE(on)-2</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -25A ; V <sub>CE</sub> = -4V		-4.0	V
Iceo	Collector Cutoff Current	V <sub>CE</sub> = -60V; I <sub>B</sub> = 0		-1.0	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0		-0.7	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	Ic= -1.5A; VcE= -4V	25		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -15A ; V <sub>CE</sub> = -4V	15	75	
f⊤	Current-Gain—Bandwidth Product	Ic= -1A; V <sub>CE</sub> = -10V;f <sub>test</sub> = 1.0MHz	3		MHz

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by SPTECH manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B